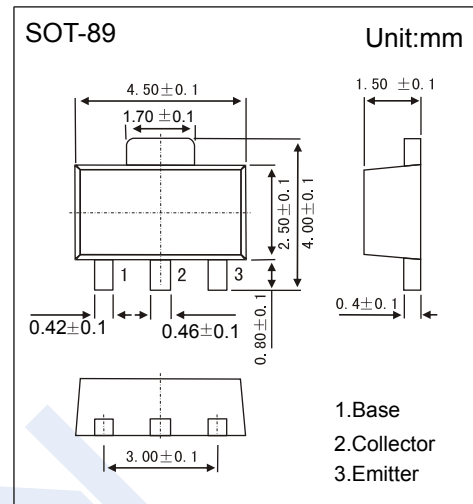


PNP Transistors

PXT3906 (KXT3906)

■ Features

- Collector Current Capability $I_C = -0.2A$
- Collector Emitter Voltage $V_{CEO} = -40V$
- Compliment to PXT3904

■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-40	V
Collector - Emitter Voltage	V_{CE0}	-40	
Emitter - Base Voltage	V_{EB0}	-6	
Collector Current - Continuous	I_C	-0.2	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 to 150	

PNP Transistors

PXT3906 (KXT3906)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E = 0	-40			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B = 0	-40			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C = 0	-6			
Collector-base cut-off current	I _{CBO}	V _{CB} = -30 V, I _E = 0			-50	nA
Collector- emitter cut-off current	I _{CEX}	V _{CE} = -30 V, V _{BE(off)} = -3V			-50	
Emitter cut-off current	I _{EBO}	V _{EB} = -6V, I _C =0			-50	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-10 mA, I _B =-1mA			-0.25	V
		I _C =-50 mA, I _B =-5mA			-0.4	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-10 mA, I _B =-1mA	-0.65		-0.85	
		I _C =-50 mA, I _B =-5mA			-0.95	
DC current gain	h _{FE}	V _{CE} = -1V, I _C = -0.1mA	60			
		V _{CE} = -1V, I _C = -1mA	80			
		V _{CE} = -1V, I _C = -10mA	100		300	
		V _{CE} = -1V, I _C = -50mA	60			
		V _{CE} = -1V, I _C = -100mA	30			
Noise figure	NF	V _{CE} =-5V, I _C =-0.1mA, f=10Hz-15.7kHz, R _S =1KΩ			4	dB
Delay time	t _d	I _C =-10mA, I _{B1} =-I _{B2} = -1mA			35	ns
Rise time	t _r				35	
Storage time	t _s				225	
Fall time	t _f				75	
Collector output capacitance	C _{ob}	V _{CB} = -5V, I _E = 0, f=1MHz			4.5	pF
Emitter capacitance	C _e	V _{EB} =-0.5V, I _C =0, f=1MHz			10	
Transition frequency	f _T	V _{CE} = -20V, I _C = -10mA, f=100MHz	250			MHz

■ Marking

Marking	2A
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